

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI

Application No.: 09/327,469

Filed: June 8, 1999

For: SEMICONDUCTOR DEVICE AND METHOD
OF MANUFACTURING THE SAME

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)
) Art Unit: 2814
)

) Examiner: G. PERALTA
) **CERTIFICATE OF MAILING**

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Susan J. Stiles

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

March 4, 2002

Dear Sir:

In response to the Examiner's non-Final Office Action mailed October 4, 2001, please
consider the following amendments and remarks in connection with the above-identified
application.

IN THE CLAIMS:

Please amend claims 2-8 and 20-21 to read as follows:

2. (Twice Amended) A method of manufacturing a semiconductor device, comprising:
- forming an amorphous semiconductor film;
 - holding a catalytic element that promotes the crystallization of said semiconductor film in contact with said semiconductor film; and
 - irradiating a laser beam shaped in a rectangle or a square while moving the laser beam from one side of said amorphous semiconductor film toward another side thereof to sequentially crystallize said amorphous semiconductor film to form a crystalline semiconductor film,
- wherein said laser beam has an irradiation area of said pulsed laser beam of 10 cm² or more.

3. (Twice Amended) A method of manufacturing a semiconductor device, comprising:
- forming an amorphous semiconductor film over a substrate having an insulating surface;

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